

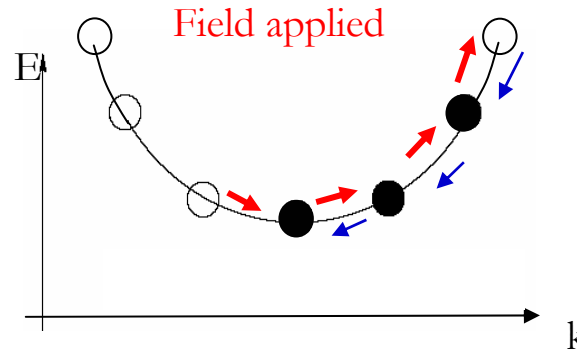
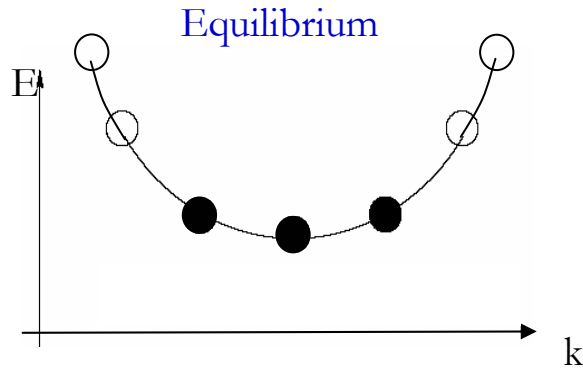
The np junction diode

LECTURE 7

- Current balancing in an np -junction at equilibrium
- Drift velocity and mobility
- Drift-Diffusion Equation
- Built-in voltage
- Carrier concentrations and potential
- Depletion Approximation

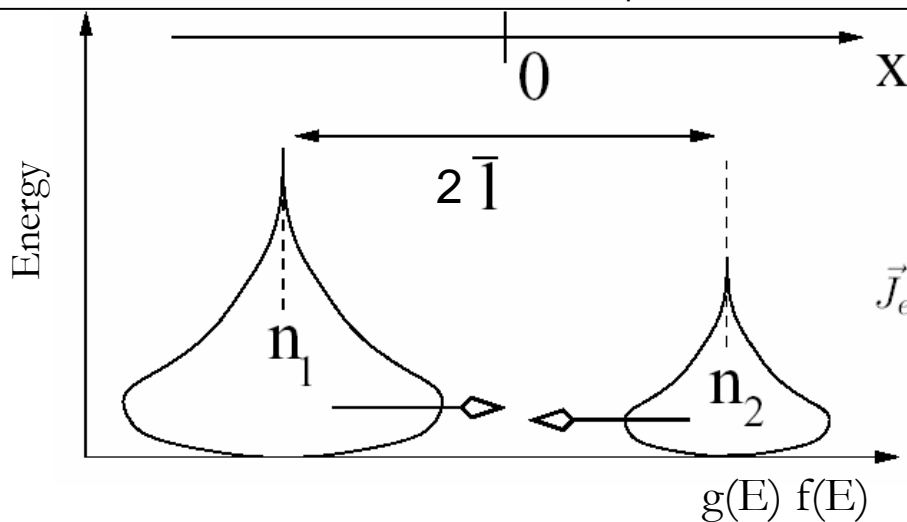
Secs.
5.5.1-2

Diffusion and drift currents



Drift current density:

$$\begin{aligned}\vec{J}_{e,\text{drift}} &= \vec{J}_{e,\text{drift}\rightarrow} + \vec{J}_{e,\text{drift}\leftarrow} \\ &= -q\frac{n}{2}(2\vec{v}_R + \vec{v}_{de}) + (-q\frac{n}{2}(-2\vec{v}_R + \vec{v}_{de})) \\ &= -qn\vec{v}_{de},\end{aligned}$$



The diffusion current density is

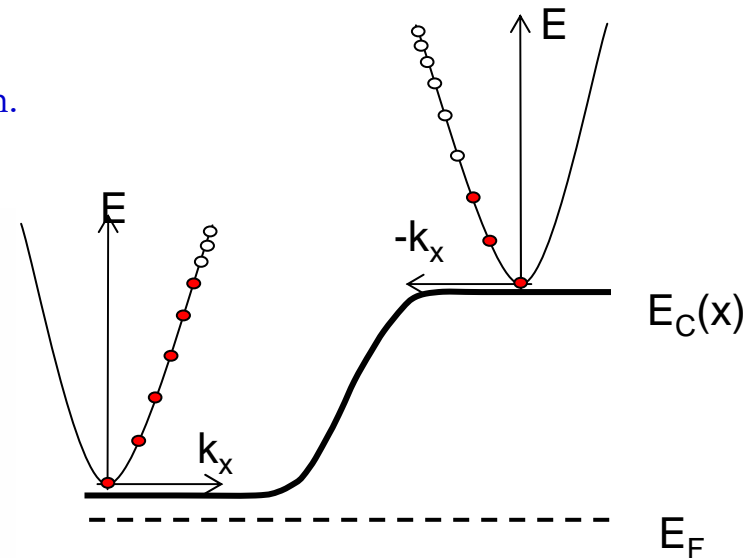
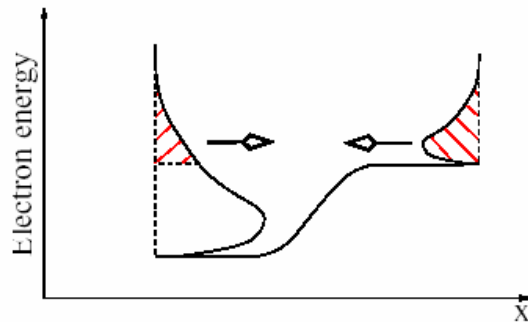
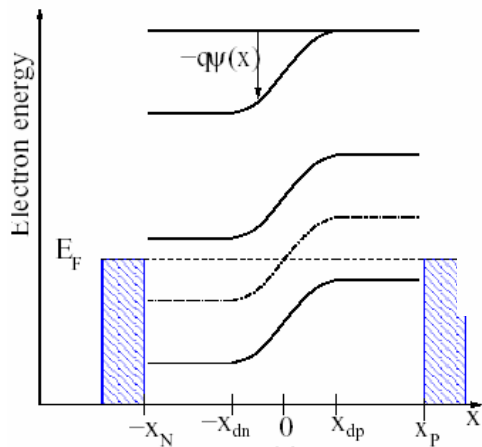
$$\vec{J}_e = -q\frac{n_1}{2}2\vec{v}_R + (-q)\frac{n_2}{2}(-2\vec{v}_R) = -q\left(\frac{n_1}{2} - \frac{n_2}{2}\right)2\vec{v}_R$$

Do
Taylor \rightarrow $q\bar{l}2v_R\frac{d\bar{n}}{dx} \equiv qD_e\frac{d\bar{n}}{dx}$

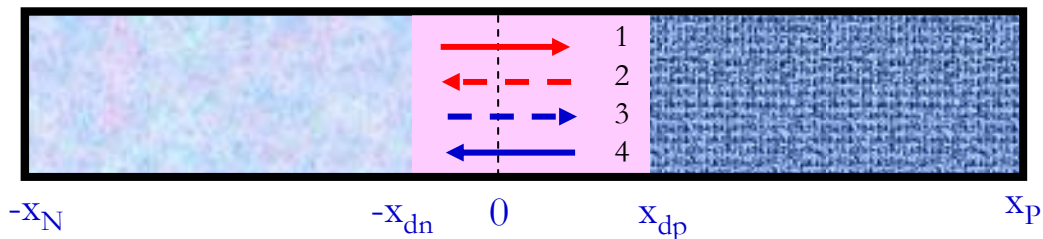
Sec. 6.1

Current balancing at equilibrium

We've already seen how to view this on an energy band diagram.



In real space we have:



What are the 3 different regions?

Match the arrows to the current components:

- | | | | |
|---|-------------------|---|------------------|
| a | $qp\vec{v}_{dh}$ | c | $qD_e \nabla n$ |
| b | $-qn\vec{v}_{de}$ | d | $-qD_h \nabla p$ |

Secs.
5.4,
5.4.1

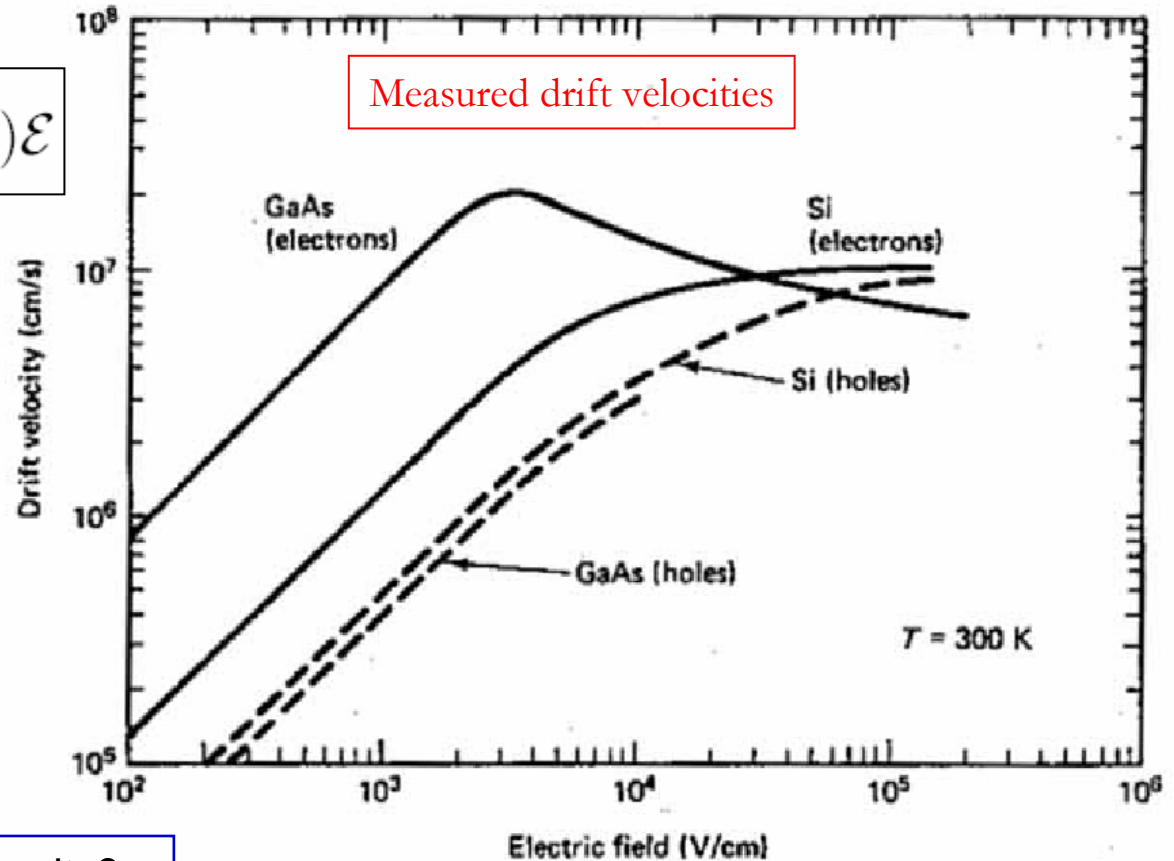
Mobility

$$v_{de}(\mathcal{E}) = |\vec{v}_{de}(\mathcal{E})| \equiv \mu_e(\mathcal{E})\mathcal{E}$$

- At low fields, the relationship is linear:

- Low-field mobility is

- Why does v_d saturate at high fields?



Does mobility depend on doping density?

μ_{e0}

μ_{h0}

Empirical equations



Secs.
5.2.2,
5.5.1,
5.5.2

DDE

For electrons

$$J_{e,x} = qn\mu_e\mathcal{E} + qD_e\frac{dn}{dx}$$

Mobility is a macroscopic parameter.

It is related to the microscopic properties of band structure and scattering.

$$\mu_e \equiv \frac{q}{m^*} \langle\langle \tau_M \rangle\rangle$$

Mobility and diffusivity are related via the Einstein Relation.

$$D_e \equiv \frac{2\mu_e}{q} \langle u_x \rangle$$

At moderate doping densities and moderate fields, what is the mean value of the x-directed KE of a carrier?

Sec. 6.1.1

Built-in voltage

At equilibrium

$$\vec{J}_e = -qn\mu_e \nabla \psi + k_B T_L \mu_e \nabla n = 0$$

Integrate

$$\int_{\psi(p\text{-side})}^{\psi(n\text{-side})} d\psi = \frac{k_B T_L}{q} \int_{n_{0p}}^{n_{0n}} \frac{1}{n} dn$$

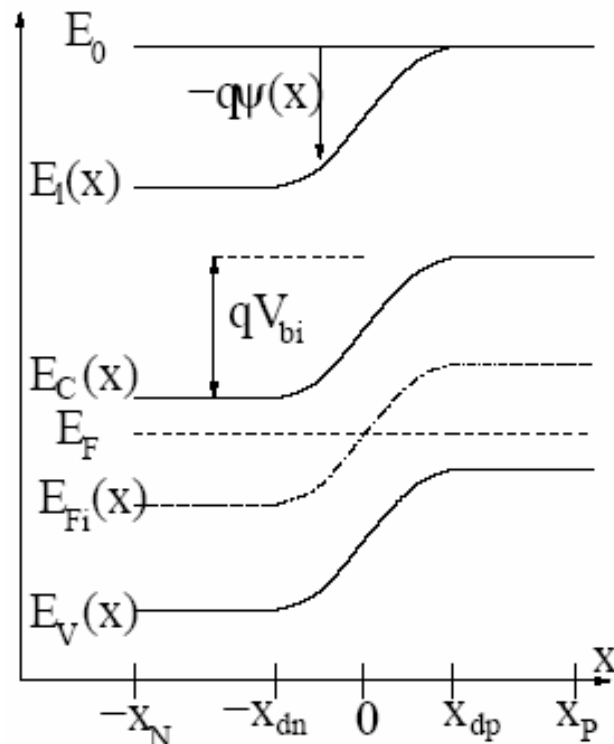
The difference in potential is the

$$V_{bi} = \frac{k_B T_L}{q} \ln \frac{n_{0n}}{n_{0p}} \equiv V_{th} \ln \left[\frac{N_D N_A}{n_i^2} \right]$$

where, we've related n_{0p} to n_i^2 (see next slide), and

$$V_{th} \equiv \frac{k_B T}{q}$$

What is the name for this voltage?



Intrinsic carrier concentration

MB statistics apply.

$$\begin{cases} n_i = N_C \exp\left(\frac{E_{Fi} - E_C}{k_B T}\right) \\ p_i = N_V \exp\left(\frac{E_V - E_{Fi}}{k_B T}\right) \end{cases}$$

Equate:

$$E_{Fi} - E_V = \frac{E_g}{2} + \frac{3k_B T}{4} \ln\left(\frac{m_{h,\text{DOS}}^*}{m_{e,\text{DOS}}^*}\right)$$

Multiply:

$$n_i = \sqrt{(N_C N_V)} \exp\left(\frac{-E_g}{2k_B T}\right)$$

Amalgamate with previous expressions for n_0 and p_0

$$\begin{cases} n_0 = n_i \exp\left(\frac{E_F - E_{Fi}}{k_B T}\right) \\ p_0 = n_i \exp\left(\frac{E_{Fi} - E_F}{k_B T}\right) \end{cases}$$

Multiply:

$$n_0 p_0 = n_i p_i = n_i^2$$

Carrier concentrations and potential

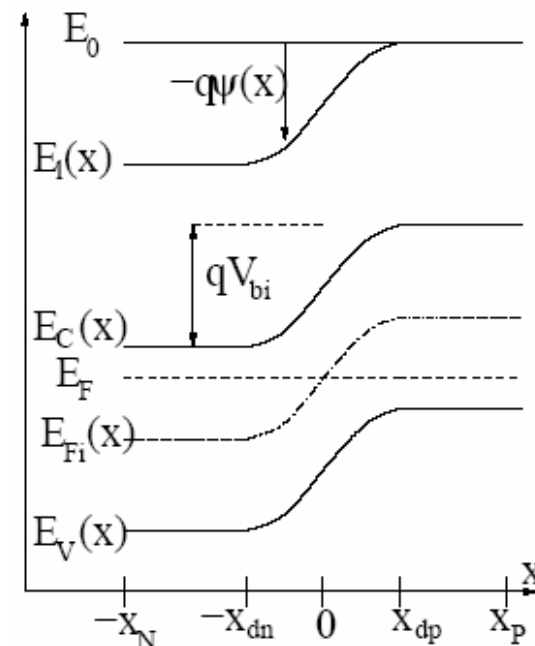
$$-q\psi(x) = E_l(x) - E_0$$

$$\left\{ \begin{array}{l} -q\psi(x) \equiv E_C(x) - E_C(x_P) \\ \text{system} \end{array} \right\}$$

Leads to concentrations in terms of potential

$$n_0(x) = n_0(x_P) e^{\psi(x)/V_{th}}$$

$$p_0(x) = p_0(x_P) \text{ [red box]}$$



Sec. 6.1.3

The potential profile

Use Poisson's Equation:

$$-\frac{d^2\psi}{dx^2} = \boxed{}$$

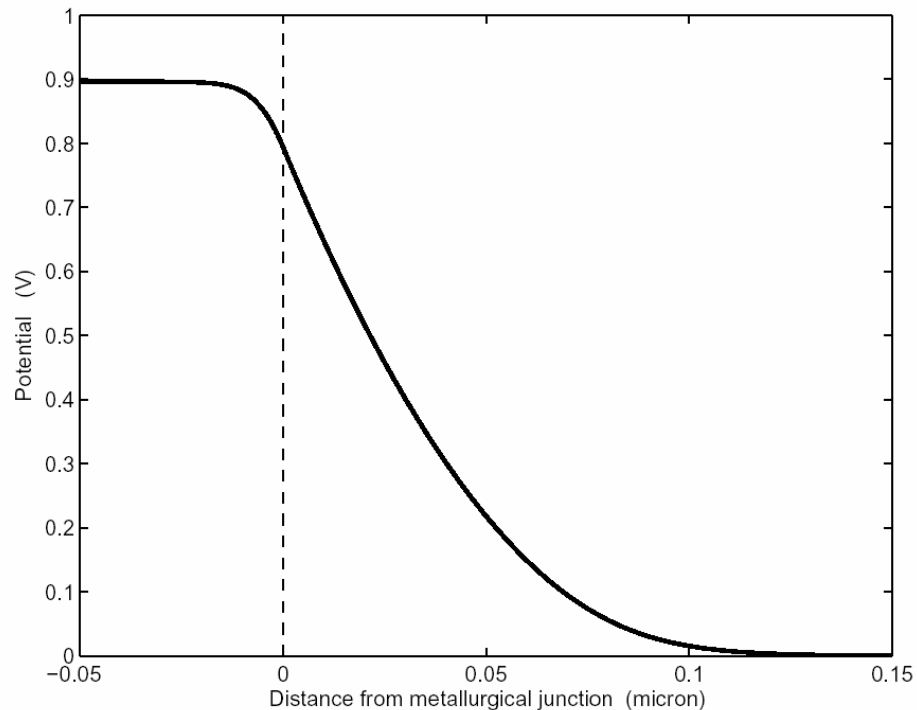
$$-\frac{d^2\psi}{dx^2} = \frac{q}{\epsilon} \left[p_0(x_P) e^{-\psi(x)/V_{th}} - n_0(x_P) e^{\psi(x)/V_{th}} + N_D - N_A \right]$$

Results for an

np-diode

$$N_D = 1E18/cc$$

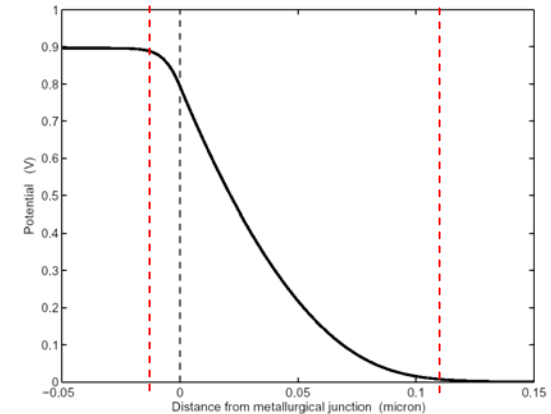
$$N_A = 1E17/cc$$



The Depletion Approximation

Sec. 6.2

- Approximate the boundaries



- Approximate the carrier concentrations within the SCR

$$n(x), p(x) \ll N_D$$

$$n(x), p(x) \ll N_A$$

$$-x_{dn} \leq x \leq 0$$

$$0 \leq x \leq x_{dp},$$

- Split the non-linear DE into two,

$$\frac{d^2\psi}{dx^2} = \frac{-qN_D}{\epsilon}$$

$$\frac{d^2\psi}{dx^2} = \frac{qN_A}{\epsilon}$$

$$-x_{dn} \leq x \leq 0$$

$$0 \leq x \leq x_{dp}.$$

- Impose BC's

$$-\frac{d\psi}{dx} = 0$$

$$x = -x_{dn}$$

$$-\frac{d\psi}{dx} = 0$$

$$x = x_{dp}$$

$$\psi = 0$$

$$x = x_{dp}.$$

- Solution is

$$\psi(-x_{dn}) - \psi(x_{dp}) \equiv V_J = \frac{q}{2\epsilon} \left[N_D x_{dn}^2 + N_A x_{dp}^2 \right]$$

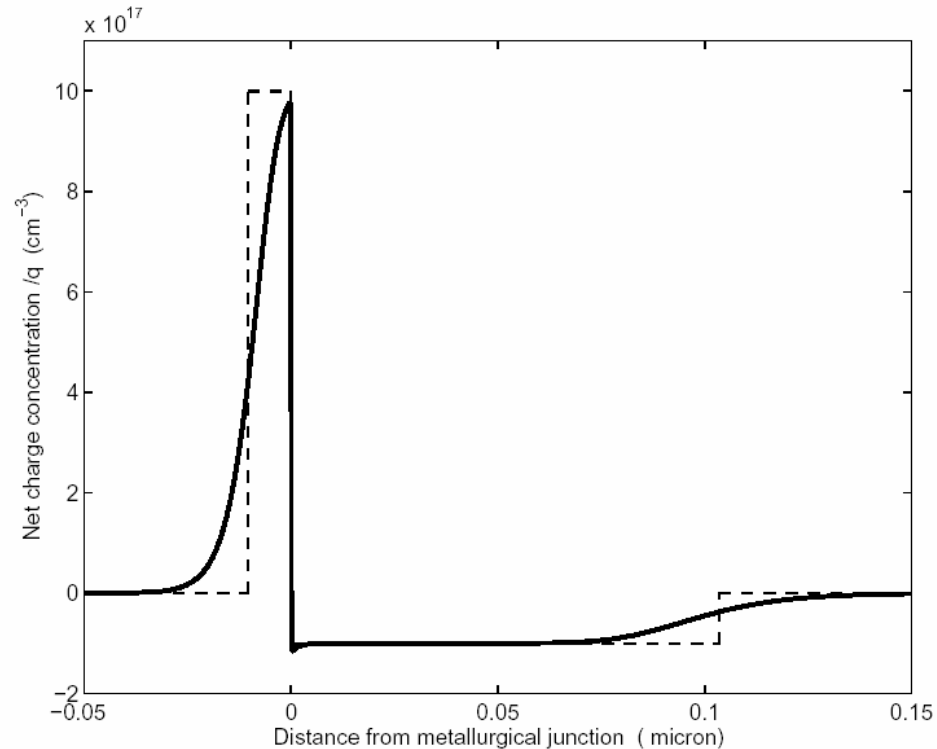
Sec. 6.2

How good is the DA?

Results for an np-diode

$$N_D = 1E18/cc$$

$$N_A = 1E17/cc$$



Overall charge neutrality

$$\longrightarrow qN_D x_{dn} A = qN_A x_{dp} A$$

Values for x_{dn} and x_{dp} ?

Depletion approximation
for the SCR width

$$W = \sqrt{\frac{2\epsilon}{q} V_J \left(\frac{1}{N_D} + \frac{1}{N_A} \right)}$$

Value for W ?